





300V PNP HIGH VOLTAGE TRANSISTOR IN SOT223

Features

- BV_{CEO} > -300V
- I_C = -0.5A Continuous Current
- I_{CM} = -1A Peak Pulse Current
- Complementary NPN Type: FZT657
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

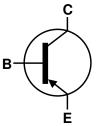
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208@3
- Weight: 0.112 grams (Approximate)

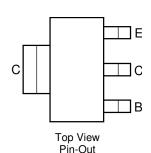




Top View



Device Symbol



Ordering Information (Note 4)

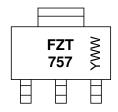
Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
FZT757TA	AEC-Q101	FZT757	7	12	1,000

Notes:

- $1.\;EU\;Directive\;2002/95/EC\;(RoHS)\;\&\;2011/65/EU\;(RoHS\;2)\;compliant.\;All\;applicable\;RoHS\;exemptions\;applied.$
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-Free, "Green" and Lead-Free.
- 3. Halogen- and Antimony-Free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

SOT223



FZT 757 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)





Absolute Maximum Ratings (@TA = +25 ℃, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-300	V
Collector-Emitter Voltage	V _{CEO}	-300	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-0.5	Α
Peak Pulse Current	I _{CM}	-1	Α

Thermal Characteristics (@TA = +25 ℃, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3.0	w	
Power Dissipation	(Note 6)	Б	2.0		
rower dissipation	(Note 7)	P _D	1.6] vv	
	(Note 8)		1.2		
	(Note 5)		41.7		
Thermal Resistance, Junction to Ambient	(Note 6)	D	62.5	°C/W	
Thermal Resistance, Junction to Ambient	(Note 7)	R _{0JA}	78.1	C/VV	
	(Note 8)		104		
Thermal Resistance, Junction to Leads (Note 9)		$R_{ heta JL}$	12.9	°C/W	
Operating and Storage Temperature Range	T _{J.} T _{STG}	-55 to +150	.€		

ESD Ratings (Note 10)

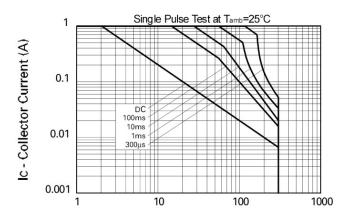
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
- 8. Same as Note 5, except the device is mounted on minimum recommended pad layout.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

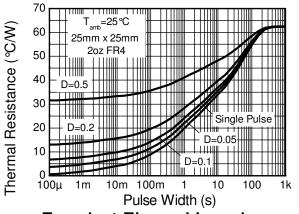


Thermal Characteristics and Derating Information

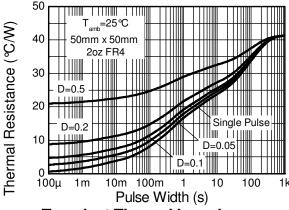


VCE - Collector Emitter Voltage (V)

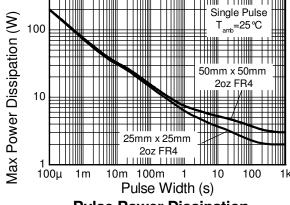
Safe Operating Area



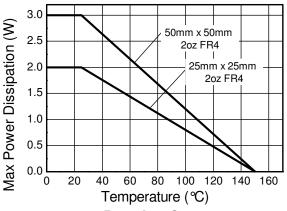
Transient Thermal Impedance



Transient Thermal Impedance



Pulse Power Dissipation



Derating Curve





Electrical Characteristics (@TA = +25 °C, unless otherwise specified.)

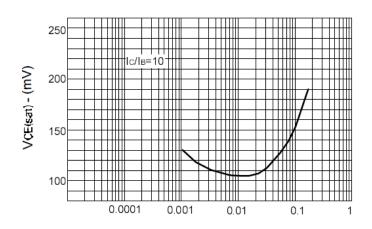
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-300	_	_	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	-300	_	_	V	$I_C = -10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	_	_	V	$I_E = -100\mu A$
Collector Cut-Off Current	I _{CBO}	_	<1	-100	nA	V _{CB} = -200V
Emitter Cut-Off Current	I _{EBO}	-	<1	-100	nA	V _{EB} = -5.6V
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}	_	-	-0.5	V	$I_C = -100 \text{mA}, I_B = -10 \text{mA}$
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	-	-	-1.0	V	$I_C = -100 \text{mA}, I_B = -10 \text{mA}$
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(on)}	-	_	-1.0	V	$I_C = -100 \text{mA}, V_{CE} = -5 \text{V}$
DC Current Gain (Note 11)	h _{FE}	40	_	_		$I_C = -10 \text{mA}, V_{CE} = -5 \text{V}$
DC Current Gain (Note 11)		50	-	_	_	I _C = -100mA, V _{CE} = -5V
Current Gain-Bandwidth Product	f _T	30			MHz	I _C = -10mA, V _{CE} = -20V, f = 20MHz
Output Capacitance	C_{obo}	_	_	20	pF	$V_{CB} = -20V$, $f = 1MHz$

Note:

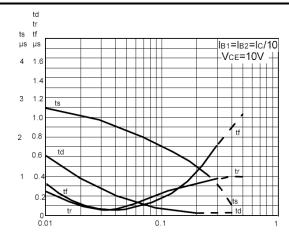
11. Measured under pulsed conditions. Pulse width ≤ 300 µs. Duty cycle ≤ 2%.



Typical Electrical Characteristics (@T_A = +25 ℃, unless otherwise specified.)



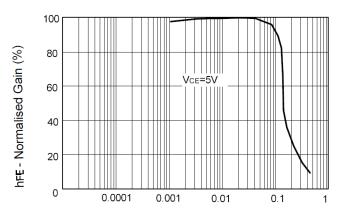
Ic - Collector Current (Amps)



Switching time

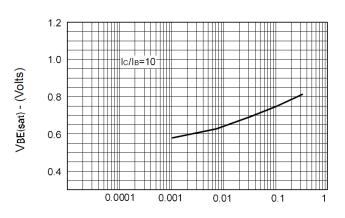
Ic - Collector Current (Amps)

VCE(sat) v IC



Ic - Collector Current (Amps)

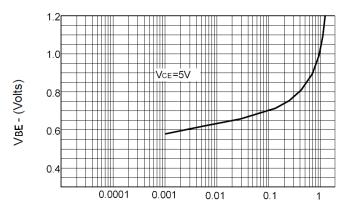
Switching Speeds



Ic - Collector Current (Amps)

VBE(sat) v IC

hFE v IC



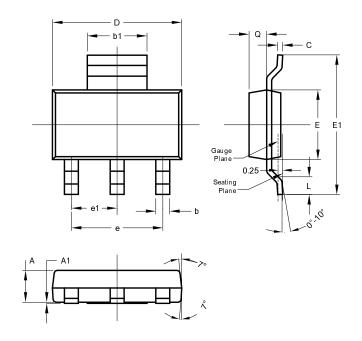
Ic - Collector Current (Amps)

VBE(on) v IC



Package Outline Dimensions

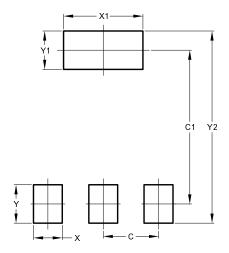
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.





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